STRONGLY CORRELATED COLLECTIVE EXCITATIONS IN QUASI-2D NANOSTRUCTURES OF METALS AND SEMICONDUCTORS

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- Biexcitons and Trions Formed by Indirect Excitons in Layered Semiconductors: Binding Energies within the Configuration Space (Landau-Herring) Approach
- Organic Molecular Semiconductor Crystals with Two Isolated Frenkel Exciton States: Frenkel-Charge-Transfer Exciton Intermixing
- Ultrathin Plasmonic Films of Finite Thickness: Plasma Frequency Spatial Dispersion and Magneto-Optical Response
- Summary

RECENT EXPERIMENTS

with Direct and Indirect Excitons in Coupled Quantum Wells (CQWs) and quasi-2D Layered van der Waals Heterostructures



TRION COMPLEXES

formed by direct (a) and indirect (b) excitons in CQWs

I.V.Bondarev, Mod. Phys. Lett. B 30, 1630006 (2016)



SCHEMATIC VIEW

of the charge-neutral spin-aligned Wigner crystal structure of two trions (also can be viewed as **triexciton** – three indirect singlet excitons)



INDIRECT EXCITONS, TRIONS, and BIEXCITONS formed by <u>indirect</u> excitons are those building blocks that control the formation of more complex Wigner-like electron-hole crystal structures in quasi-2D layered van der Waals bound semiconductor heterostructures

BIEXCITON AND TRION FORMED BY INDIRECT EXCITONS

Theoretical Description of the Ground State within the Configuration Space Approach (atomic units)



$$\mathbf{V}_{\mathbf{p}_1\mathbf{p}_2} \sim d^2/\Delta \rho^3$$



$$\hat{H}(\rho_{1},\rho_{2},\Delta\rho,d) = -\frac{1}{\rho_{1}}\frac{\partial}{\partial\rho_{1}}\rho_{1}\frac{\partial}{\partial\rho_{1}} - \frac{1}{\rho_{2}}\frac{\partial}{\partial\rho_{2}}\rho_{2}\frac{\partial}{\partial\rho_{2}}$$

$$\frac{1}{\sqrt{\rho_{1}^{2}+d^{2}}} - \frac{1}{\sqrt{\rho_{2}^{2}+d^{2}}} - \frac{1}{\sqrt{(\rho_{1}-\Delta\rho)^{2}+d^{2}}} - \frac{1}{\sqrt{(\rho_{2}+\Delta\rho)^{2}+d^{2}}}$$
Exact solution available: *R.P.Leavitt & J.W.Little, PRB 42, 11774 (1990)*

$$\frac{2 e_{1}-h_{2}}{\sqrt{[(\rho_{1}+\sigma\rho_{2})/\lambda-\Delta\rho]^{2}+d^{2}}} - \frac{2 e_{2}-h_{1}}{\sqrt{[(\sigma\rho_{1}+\rho_{2})/\lambda+\Delta\rho]^{2}+d^{2}}}$$

$$+ \frac{2 h_{1}-h_{2}}{|\sigma(\rho_{1}-\rho_{2})/\lambda+\Delta\rho|} + \frac{2 e_{1}-e_{2}}{|(\rho_{1}-\rho_{2})/\lambda-\Delta\rho|}$$
negative trion

$$\lambda = 1+\sigma; \quad \overline{\sigma = m_{e}/m_{h} \rightarrow 1}$$
due to the mass reversal effect

$$Ry^{*} = \frac{\hbar^{2}}{2\mu a_{B}^{*2}} = \frac{\mu(\ln m_{0})}{\varepsilon^{2}} 13.6 \text{ eV}; \quad a_{B}^{*} = \frac{\varepsilon}{\mu} 0.529 \text{ Å}$$

SCHEMATIC VIEW of the Tunnel Exchange Coupling Configuration for Two Ground-State Indirect Excitons to Form the Trion or Biexciton Complex



Trion Binding Energy $E_{X^*} = E_g - 2E_X = -J_{X^*}(\Delta \rho_0)$

$$J_{X*}(\Delta \rho) = \int_{-\Delta \rho/\sqrt{2}}^{\Delta \rho/\sqrt{2}} \left| \psi_{X*}(x,y) \frac{\partial \psi_{X*}(x,y)}{\partial x} \right|_{x=0} dy$$

 $\psi_{X*}(x,y) = \psi_{IX}(\rho_1(x,y),d) \psi_{IX}(\rho_2(x,y),d) exp(-S_{X*}(x,y))$

Biexciton Binding Energy $E_{XX} = E_g - 2E_X = -J_{XX}(\Delta \rho_0)$

$$\left(J_{XX}(\Delta \rho) = \frac{2}{3!} \int_{-\Delta \rho/\sqrt{2}}^{\Delta \rho/\sqrt{2}} \left| \psi_{XX}(x,y) \frac{\partial \psi_{XX}(x,y)}{\partial x} \right|_{x=0} dy$$

I.V.Bondarev, Mod. Phys. Lett. B 30, 1630006 (2016); PRB 90, 245430 (2014); PRB 83, 153409 (2011)

BIEXCITON AND TRION FORMED BY INDIRECT EXCITONS Ground State Binding Energies Calculated using the Configuration Space (Landau-Herring) Method



PHYSICAL REVIEW B 97, 165419 (2018)

Complexes of dipolar excitons in layered quasi-two-dimensional nanostructures

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Stability of trions in coupled quantum wells modeled by two-dimensional bilayers

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TRIONS FORMED BY INDIRECT EXCITONS Latest Experiments @ HARVARD

L.A.Jauregui, A.Y.Joe, K.Pistunova, D.S.Wild, A.A.High, Y.Zhou, G.Scuri, K.De Greve, A.Sushko, C.-H.Yu, T.Taniguchi, K.Watanabe, D.J.Needleman, M.D.Lukin, H.Park, & P.Kim, arXiv:1812.08691



Our measurements in the doped regime can be explained by the formation of charged IEs (CIEs) (21). As shown in the normalized reflection measured with the same gating scheme, we can identify the p/intrinsic, intrinsic/intrinsic, intrinsic/n regions by the disappearance of the absorption dips for intralayer excitons in MoSe₂ and WSe₂ (22), which are well aligned with the sudden red shift observed in IE PL (vertical dashed lines). Thus, this jump in energy can be related to the CIE. We note that charged excitons can be referred to trions (23-26), three-body bound states, or alternatively, attractive polarons, excitonic states dressed by a polarized fermionic sea (27, 28), similar in monolayer TMDs. The value of the observed jump \approx 10 meV (15 meV) for positive (negative) CIEs is in good agreement with the calculated binding energy of CIEs (21)). The lifetime of CIEs is \approx 100 ns near the band edge, decreasing with increasing doping presumably due to additional decay channels enabled by scattering with free carriers (Figure 1g).



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Experimental Data I

Crystalline CuPc on a glass substrate vs CuPc in solution (NCSU data)



Quantum Theory of the Frenkel-CT Exciton Intermixing

Solving the Eigen-Value Problem for the Hamiltonian of the Two Frenkel Excitons Coupled Individually to the CT exciton

$$\begin{split} \hat{H}\{k\text{-space}\} &= \sum_{k} \left(\hat{H}_{k}^{F} + \hat{H}_{k}^{CF} + \hat{H}_{k}^{FC} + \hat{H}_{k}^{FC} \right), \\ \hat{H}_{k}^{F} &= \sum_{\nu=0,1} \Delta_{F}^{\nu} B_{k\nu}^{\dagger} B_{k\nu}, \quad H_{k}^{FF} = \sum_{\nu=0,1} L_{k}^{\nu\nu'} B_{k\nu}^{\dagger} B_{k\nu'}, \\ \hat{H}_{k}^{F} &= \sum_{\nu=0,1} \Delta_{V}^{\nu} B_{k\nu}^{\dagger} B_{k\nu}, \quad H_{k}^{FF} = \sum_{\nu=0,1} L_{k}^{\nu\nu'} B_{k\nu}^{\dagger} B_{k\nu'}, \\ L_{k}^{\nu\nu'} &\approx 2M \, s_{\nu} s_{\nu'} \cos k, \quad s_{\nu} &= \left\langle \chi_{n}^{1\nu} \middle| \chi_{n}^{00} \right\rangle, \quad s_{\nu}^{2} = F_{0\nu} = \frac{g^{2\nu}}{\nu!} e^{-g^{2}} (\text{if } g \approx 1, \text{ then } s_{0} \approx s_{1} \approx 0.6 = s) \\ \hat{H}_{k}^{C} &= \Delta_{CT} \left(\tilde{C}_{kg}^{\dagger} \tilde{C}_{kg} + \tilde{C}_{ku}^{\dagger} \tilde{C}_{ku} \right), \quad H_{k}^{FC} &= \sum_{\nu=0,1} \sqrt{2} \varepsilon_{k} s_{\nu} B_{k\nu}^{\dagger} \tilde{C}_{kg} + h.c., \quad \varepsilon_{k} = \sqrt{\varepsilon_{+}^{2} \cos^{2} \frac{k}{2} + \varepsilon_{-}^{2} \sin^{2} \frac{k}{2}}, \quad \varepsilon_{\pm} = \varepsilon_{e} \pm \varepsilon_{h} \\ \tilde{\xi}_{\nu\mu}(k) &= u_{\nu\mu}^{*}(k) B_{k\nu} + c_{\nu}^{*}(k) \tilde{C}_{kg}, \quad \nu = 0, 1; \quad \mu = 1, 2 \\ \hat{H} &= \sum_{\mu=1,2} \sum_{\nu=0,1} \sum_{k} \hbar \omega_{\nu\mu}(k) \xi_{\nu\mu}^{\dagger}(k) \xi_{\nu\mu}(k) \xi_{\nu\mu}(k) + E_{0} \\ \hbar \omega_{\nu\mu}(k) &= \hbar \omega_{\nu 1,2}(k) = \hbar \omega_{\nu}^{(\pm)}(k) = \frac{1}{2} \left(D_{k}^{\nu\nu} + \Delta_{CT} \pm \sqrt{(D_{k}^{\nu\nu} - \Delta_{CT})^{2} + 8(s_{\nu}\varepsilon_{k})^{2}} \right), \\ D_{k}^{\nu\nu'} &= \Delta_{F}^{\nu} \delta_{\nu\nu'} + 2M s_{\nu} s_{\nu'} \cos k \\ E_{F1} &= D_{0}^{00}, \quad E_{F2} = D_{0}^{11}, \quad E_{\nu}^{(\pm)} = \hbar \omega_{\nu}^{(\pm)}(0), \quad \nu = 0, 1 \end{split}$$

Comparison of the Theory with the Experiment



Calculated Frenkel-CT Exciton Splitting and Intermixing

as a function of the Intermolecular Coupling Constant



I.V.Bondarev, A.Popescu, R.A.Younts, B.Hoffman, T.McAfee, D.B.Dougherty, K.Gundogdu, and H.W.Ade, Appl. Phys. Lett. 109, 213302 (2016)

Monitoring Charge Separation Processes in Crystalline Organic Molecular Semiconductor Thin Films (CuPc)



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ULTRATHIN PLASMONIC FILMS OF FINITE THICKNESS. **EFFECTS OF QUANTUM CONFINEMENT**

Keldysh-Rytova Potential

Coulomb interaction in thin semiconductor and semimetal films

L. V. Keldysh

P. N. Lebedev Physics Institute, USSR Academy of Sciences

L.V.Keldysh, JETP Lett. 29, 658 (1980) N.S.Rytova, Moscow State University Physics Bulletin 3, 30 (1967)

(Submitted 28 April 1979)

$$V(\vec{\rho}, z, z') = \frac{4\pi e e'}{\epsilon} \int \frac{d^2 k}{(2\pi)^2} e^{2\mathbf{k}\vec{\rho}} \frac{\operatorname{ch}\left[\left|\mathbf{k}\right| \left(\frac{d}{2} - z\right) + \eta_2\right] \operatorname{ch}\left[\left|\mathbf{k}\right| \left(\frac{d}{2} + z'\right) + \eta_1\right]}{\left|\mathbf{k}\right| \operatorname{sh}\left[\left|\mathbf{k}\right| d + \eta_1 + \eta_2\right]}$$
$$\eta_{1,2} = \frac{1}{2} \ln \frac{\epsilon + \epsilon_{1,2}}{\epsilon - \epsilon_{1,2}}.$$



$$V(\vec{\rho}) = \frac{2ee'}{\epsilon d} \int_{0}^{\infty} \frac{J_{o}(t)dt}{t + \frac{\epsilon_{1} + \epsilon_{2}}{\epsilon} \frac{\rho}{d}}$$

$$d << \rho = \frac{\pi ee'}{\epsilon d} \left[\mathcal{H}_{o} \left(\frac{\epsilon_{1} + \epsilon_{2}}{\epsilon} - \frac{\rho}{d} \right) - N_{o} \left(\frac{\epsilon_{1} + \epsilon_{2}}{\epsilon} - \frac{\rho}{d} \right) \right]$$

€d

PLASMA FREQUENCY SPATIAL DISPERSION AND NONLOCAL OPTICAL RESPONSE OF ULTRATHIN PLASMONIC FILMS Momentum Space





For thin enough plasmonic films, one has $N_{3D}d = N_{2D}$, so that Eq. (9) can be written as

$$\omega_p = \omega_p(k) = \frac{\omega_p^{3D}}{\sqrt{1 + (\varepsilon_1 + \varepsilon_2)/\varepsilon kd}}.$$
(11)

If $(\varepsilon_1 + \varepsilon_2)/\varepsilon kd \ll 1$ (relatively thick film), then $\omega_p = \omega_p^{3D}$ of Eq. (10), whereas one has

$$\omega_p = \omega_p^{2D}(k) = \sqrt{\frac{4\pi e^2 N_{2D} k}{(\varepsilon_1 + \varepsilon_2)m^*}}$$
(12)

if $(\varepsilon_1 + \varepsilon_2)/\varepsilon kd \gg 1$ (ultrathin film), which agrees precisely with the plasma frequency spatial dispersion of the 2D electron gas in air (see, e.g., Ref. [33]), but does show the explicit dependence on bottom (ε_1) and top (ε_2) surrounding materials.



⁾ Optical Response Nonlocality

$\left[\begin{array}{c} \hline d \\ \hline \end{array}\right]$



I.V.Bondarev and V.M.Shalaev, Opt. Mater. Express 7, 3731 (2017)

PLASMA FREQUENCY SPATIAL DISPERSION AND NONLOCAL OPTICAL RESPONSE OF ULTRATHIN PLASMONIC FILMS Coordinate Space

ULTRATHIN PLASMONIC FILMS OF FINITE THICKNESS. EFFECTS OF QUANTUM CONFINEMENT

Comparison with Experiments



(a,b) Schematic of the confined thin film geometry (a) and the normalized Coulomb interaction potential (b) for ultrathin finite thickness plasmonic films. (c) Thin film plasma frequency normalized by the bulk plasma frequency derived theoretically in Ref.[1]. (d) Plasma frequency extracted from the ellipsometry measurements done on ultrathin TiN films of controlled variable thickness fabricated at Purdue University [2].
 [1] I.V.Bondarev and V.M.Shalaev, Opt. Mater. Express 7, 3731 (2017); [2] D.Shah, et al., Adv. Opt. Mater. 1700065 (2017)

PLASMA FREQUENCY SPATIAL DISPERSION & MAGNETO-OPTICAL RESPONSE OF ULTRATHIN PLASMONIC FILMS OF FINITE THICKNESS

L.D.Landau & E.M.Lifshitz, *Electrodynamics of Continuous Media*, 2nd edn., 1984

When spatial dispersion is present, the permittivity is a tensor, not a scalar, even in an isotropic medium: a distinctive direction is generated by the wave vector. If the medium not only is isotropic but also has a centre of symmetry, the tensor ε_{ik} must be constructed from the components of the vector **k** and the unit tensor δ_{ik} (in the absence of a centre of symmetry, there may also be a term containing the antisymmetric unit tensor e_{ikl} ; see §104). The general form of such a tensor may be written as

$$\varepsilon_{ik}(\omega, \mathbf{k}) = \varepsilon_t(\omega, k)(\delta_{ik} - k_i k_k/k^2) + \varepsilon_l(\omega, k)k_i k_k/k^2, \qquad (103.12)$$

where ε_t and ε_l depend only on the magnitude of the wave vector (and on ω). If E is parallel to the wave vector, then $\mathbf{D} = \varepsilon_l \mathbf{E}$; if $\mathbf{E} \perp \mathbf{k}$, then $\mathbf{D} = \varepsilon_t \mathbf{E}$. The quantities ε_l and ε_t are accordingly called the *longitudinal* and *transverse permittivities*. When $\mathbf{k} \rightarrow 0$, the expression (103.12) should tend to $\varepsilon(\omega)\delta_{ik}$, which does not depend on the direction of \mathbf{k} ; it is therefore clear that

$$\varepsilon_l(\omega, 0) = \varepsilon_t(\omega, 0) = \varepsilon(\omega). \tag{103.13}$$

The description of the electromagnetic properties of an isotropic medium by means of the permittivities ε_l and ε_r corresponds to Maxwell's equations written in the form (103.3) and (103.4). On the other hand, as $\mathbf{k} \to 0$ and the spatial dispersion disappears, we can revert to the description by means of ε and μ . There is consequently a certain relation between these quantities (see Problem 1).

PLASMA FREQUENCY SPATIAL DISPERSION & MAGNETO-OPTICAL RESPONSE OF ULTRATHIN PLASMONIC FILMS OF FINITE THICKNESS

L.D.Landau & E.M.Lifshitz, *Electrodynamics of Continuous Media*, 2nd edn., 1984

PROBLEM 1. Find the relation between the functions $\varepsilon(\omega)$, $\mu(\omega)$ and the limiting values of $\varepsilon_l(\omega, k)$ and $\varepsilon_l(\omega, k)$ as $k \to 0$.

SOLUTION. We compare the expressions for the averaged microscopic current $\bar{\rho}\bar{v}$ in the forms (103.5) and (79.3). For a monochromatic field, we have in the first case

$$\overline{\rho v}_{i} = -i\omega [\varepsilon_{ik}(\omega, \mathbf{k}) - \delta_{ik}] E_{k}/4\pi,$$

and in the second case

$$\overline{\rho \mathbf{v}} = -i\omega [\varepsilon(\omega) - 1] \mathbf{E}/4\pi + ic [\mu(\omega) - 1] \mathbf{k} \times \mathbf{H}/4\pi.$$

Substituting in the first $\varepsilon_{ik}(\omega, \mathbf{k})$ from (103.12), and in the second $\mathbf{H} = c\mathbf{k} \times \mathbf{E}/\omega\mu$ in accordance with Maxwell's equation, and equating the two expressions (for $k \to 0$), we find

$$1 - \frac{1}{\mu(\omega)} = \frac{\omega^2}{c^2} \lim_{k \to 0} \frac{\varepsilon_t(\omega, k) - \varepsilon_l(\omega, k)}{k^2}$$

by comparing the terms in $k(k \cdot E)$. Together with (101.13), this gives the required relation

MAGNETO-OPTICAL RESPONSE OF ULTRATHIN PLASMONIC FILMS OF FINITE THICKNESS Possibility for Negative Refraction



QED EFFECT example – Dipolar Spontaneous Decay



$$\begin{aligned} \hat{E}_{\alpha}(\mathbf{r},\omega) &= i \frac{4\pi\omega^2}{c^2} \int d\mathbf{r}' \sum_{\lambda=x,y,z} G_{\alpha\lambda}(\mathbf{r},\mathbf{r}',\omega) \hat{J}_{\lambda}(\mathbf{r}',\omega) + \text{h.c.}, \\ \hat{J}_{\lambda}(\mathbf{r},\omega) &= \sqrt{\text{Im}\,\varepsilon_{\lambda\lambda}(\mathbf{r},\omega)/\pi} \,\hat{f}_{\lambda}(\mathbf{r},\omega) \\ &[\hat{f}_{\lambda}(\mathbf{r},\omega), \hat{f}_{\lambda'}^{\dagger}(\mathbf{r}',\omega')] = \delta_{\lambda\lambda'} \,\delta(\mathbf{r}-\mathbf{r}') \,\delta(\omega-\omega') \\ &\Gamma(\mathbf{r}_{A},\omega) &= \frac{8\pi\omega^2}{\hbar c^2} \sum_{\alpha,\lambda=x,y,z} \left\langle \hat{d}_{\alpha} \hat{d}_{\lambda}^{\dagger} \right\rangle \text{Im}\,G_{\alpha\lambda}(\mathbf{r}_{A},\mathbf{r}_{A},\omega) \sim \mathbf{r}_{s,p}^{prop} \& \mathbf{r}_{s,p}^{evan} \\ &\sum_{\beta=x,y,z} \left(\nabla \times \nabla \times - \omega^2 \hat{\varepsilon}(\mathbf{r},\omega)/c^2 \right)_{\alpha\beta} G_{\beta\lambda}(\mathbf{r},\mathbf{r}',\omega) = \delta_{\alpha\lambda}(\mathbf{r}-\mathbf{r}') \quad \text{Multilayers:} \\ &M.S.Thomas, PRA 51, 2545 (1995) \end{aligned}$$

(a)

2

5

(b)

 $(\omega_p^{3D/c}) z_A$

15

 z_A (nm)

10

20

— Total
— Evanescent

8

 $d = 60 \,\mathrm{nm}$

..... xx

 $d=10\,\mathrm{nm}$

 $d=20\,\mathrm{nm}$

..... xx

25

 $- d = 60 \, \text{nm}$

10

30

3.0

2.5

2.0 ⁰」/₋1.5

1.0

140

120

100 80

⁰1/1

40

20

0

0









EXPLORING EFFECTS OF ANISOTROPY Finite-Thickness Effects in Plasmonic Films with Cylindrical Anisotropy



Aligned Carbon Nanotube Films (cross-sectional view): Jun Kono group @ Rice; Abram Falk @ IBM; Jon Fan group @ Stanford; see, e.g., Nano Lett. 19, 3131 (2019)



I.V.Bondarev, Opt. Mater. Express 9, 285 (2019)

One can see that $\omega_p(0, k_{\perp}) = \omega_p(k_{\perp}) = 0$ due to the properties of the modified cylindrical Bessel functions, while $\omega_p(q, 0) = \omega_p(q) \neq 0$ and is strongly thickness dependent. No plasma oscillations occur and the film behaves as a dielectric in the direction perpendicular to the cylinder alignment (*x*-direction in Fig. 1). There are plasma oscillations in the cylinder alignment direction (*y*-direction in Fig. 1), in which case the plasma frequency takes the form

$$\omega_p(q) = \omega_p^{3D} \sqrt{\frac{2qRI_0(qR)K_0(qR)}{1 + (\varepsilon_1 + \varepsilon_2)/\varepsilon qd}},$$
(7)

where $\omega_p^{3D} = \sqrt{4\pi e^2 N_{3D}/\varepsilon m^*}$ is the *effective* bulk plasma frequency of the film material $(N_{3D} = N_{2D}/d$ being the *volumetric* electron density), whereby the film behaves as a spatially dispersive metal with the dispersion character controlled by the thickness *d* and by the relative dielectric constant $(\varepsilon_1 + \varepsilon_2)/\varepsilon$ of the film. Specifically, if $(\varepsilon_1 + \varepsilon_2)/\varepsilon qd \ll 1$ (relatively thick film), then

$$\omega_p(q) = \omega_p^{3D} \sqrt{2qRI_0(qR)K_0(qR)},\tag{8}$$

whereas one has

$$\omega_p(q) = \omega_p^{2D}(q) = q \sqrt{\frac{8\pi e^2 N_{2D} R I_0(qR) K_0(qR)}{(\varepsilon_1 + \varepsilon_2)m^*}} \tag{9}$$

if $(\varepsilon_1 + \varepsilon_2)/\varepsilon qd \gg 1$ (ultrathin film), whose *q*-dependence is different, independent of the material of the film and does show the explicit dependence on the substrate and superstrate

Thickness Controlled Unidirectional Spontaneous Emission Enhancement



$$\varepsilon_{\parallel}(\omega,q) = \varepsilon \left(1 - \frac{\omega_p^2(q)}{\omega^2 + i\gamma\omega} \right)$$

SUMMARY

- > <u>TOPIC I</u>: Biexcitons and Trions Formed by Indirect Excitons in Layered Semiconductors
 - The configuration space (Landau-Herring) method to evaluate the ground-state binding energies of the neutral and charged exciton complexes (biexciton and trion)
 - Trion and biexicton binding energies can be significant, up to a few tens of meV, with the trion always having a greater binding energy than the biexciton
 - Important for non-linear optics and spin-optronics applications
- > <u>TOPIC II</u>: Organic Molecular Semiconductor Crystals with Two Frenkel Exciton States
 - Frenkel-Charge-Transfer intermixing theory to explain optical spectroscopy data
 - Important for the proper interpretation of optical properties of crystalline transition metal phthalocyanines organic semiconductors for advanced optoelectronics
- > <u>TOPIC III</u>: Transdimentional Effects in Ultrathin Metallic Films of Finite Thickness
 - Plasma frequency spatial dispersion to result in nonlocal dielectric response
 - Negative refraction, resonance magnetic response, and novel QED effects (biexponential spontaneous decay)
 - Important for the field of plasmonics and optical metasurfaces

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I.V.Bondarev, H.Mousavi & V.M.Shalaev, arXiv1908.00640v1 (2019) I.V.Bondarev, <u>Optical Materials Express</u> 9, 285 (2019) I.V.Bondarev & M.R.Vladimirova, <u>Phys. Rev. B</u> 97, 165419 (2018) I.V.Bondarev, H.Mousavi & V.M.Shalaev, <u>MRS Communications</u> 8, 1092 (2018) I.V.Bondarev & V.M.Shalaev, <u>Optical Materials Express</u> 7, 3731 (2017) A.Popescu, R.A.Younts, B.Hoffman, T.McAfee, D.B.Dougherty, H.W.Ade, K.Gundogdu, & I.V.Bondarev, <u>Nano Letters</u> 17, 6056 (2017) I.V.Bondarev, A.Popescu, R.A.Younts, B.Hoffman, T.McAfee, D.B.Dougherty, K.Gundogdu, & H.W.Ade, <u>Appl. Phys. Lett.</u> 109, 213302 (2016) I.V.Bondarev, <u>Modern Physics Letters B</u> 30, 1630006 (2016) I.V.Bondarev, <u>Phys. Rev. B</u> 90, 245430 (2014) I.V.Bondarev, <u>Phys. Rev. B</u> 83, 153409 (2011)

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